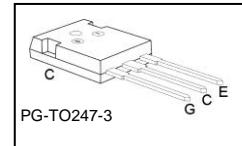
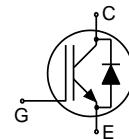


Low Loss DuoPack : IGBT in TRENCHSTOP™ and Fieldstop technology with soft, fast recovery anti-parallel Emitter Controlled HE diode


Features:

- Very low $V_{CE(sat)}$ 1.5V (typ.)
- Maximum Junction Temperature 175°C
- Short circuit withstand time 5μs
- Designed for :
 - Frequency Converters
 - Uninterruptible Power Supply
- TRENCHSTOP™ and Fieldstop technology for 600V applications offers :
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - very high switching speed
 - low $V_{CE(sat)}$
- Positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Very soft, fast recovery anti-parallel Emitter Controlled HE diode
- Qualified according to JEDEC¹ for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	V_{CE}	I_C	$V_{CE(sat), T_j=25^\circ C}$	$T_{j,max}$	Marking	Package
IKW30N60T	600V	30A	1.5V	175°C	K30T60	PG-T0247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j \geq 25^\circ C$	V_{CE}	600	V
DC collector current, limited by $T_{j,max}$	I_C	45 39	A
$T_C = 25^\circ C$, value limited by bondwire			
$T_C = 100^\circ C$			
Pulsed collector current, t_p limited by $T_{j,max}$	$I_{C,puls}$	90	
Turn off safe operating area, $V_{CE} = 600V$, $T_j = 175^\circ C$, $t_p = 1\mu s$	-	90	
Diode forward current, limited by $T_{j,max}$	I_F	45 39	
$T_C = 25^\circ C$, value limited by bondwire			
$T_C = 100^\circ C$			
Diode pulsed current, t_p limited by $T_{j,max}$	$I_{F,puls}$	90	
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time ²⁾ $V_{GE} = 15V$, $V_{CC} \leq 400V$, $T_j \leq 150^\circ C$	t_{sc}	5	μs
Power dissipation $T_C = 25^\circ C$	P_{tot}	187	W
Operating junction temperature	T_j	-40...+175	
Storage temperature	T_{stg}	-55...+150	$^\circ C$
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

¹ J-STD-020 and JESD-022

²⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.80	K/W
Diode thermal resistance, junction – case	R_{thJCD}		1.05	
Thermal resistance, junction – ambient	R_{thJA}		40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0\text{V}, I_C=0.2\text{mA}$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$V_{GE} = 15\text{V}, I_C=30\text{A}$	-	1.5	2.05	
		$T_j=25^\circ\text{C}$	-	1.9	-	
Diode forward voltage	V_F	$V_{GE}=0\text{V}, I_F=30\text{A}$	-	1.65	2.05	
		$T_j=25^\circ\text{C}$	-	1.6	-	
Gate-emitter threshold voltage	$V_{GE(\text{th})}$	$I_C=0.43\text{mA}, V_{CE}=V_{GE}$	4.1	4.9	5.7	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600\text{V}, V_{GE}=0\text{V}$	-	-	-	
		$T_j=25^\circ\text{C}$	-	-	40	μA
		$T_j=175^\circ\text{C}$	-	-	2000	
Gate-emitter leakage current	I_{GES}	$V_{CE}=0\text{V}, V_{GE}=20\text{V}$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20\text{V}, I_C=30\text{A}$	-	16.7	-	S
Integrated gate resistor	R_{Gint}			-	-	Ω

Dynamic Characteristic

Input capacitance	C_{iss}	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$	-	1630	-	pF
Output capacitance	C_{oss}		-	108	-	
Reverse transfer capacitance	C_{rss}		-	50	-	
Gate charge	Q_{Gate}	$V_{CC}=480\text{V}, I_C=30\text{A}, V_{GE}=15\text{V}$	-	167	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13	-	nH
Short circuit collector current ¹⁾	$I_{C(\text{SC})}$	$V_{GE}=15\text{V}, t_{SC}\leq 5\mu\text{s}, V_{CC} = 400\text{V}, T_j = 150^\circ\text{C}$	-	275	-	A

¹⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=30\text{A}$, $V_{GE}=0/15\text{V}$,	-	23	-	ns
Rise time	t_r	$r_G=10.6\Omega$,	-	21	-	
Turn-off delay time	$t_{d(off)}$	$L_\sigma=136\text{nH}$, $C_\sigma=39\text{pF}$	-	254	-	
Fall time	t_f	L_σ , C_σ from Fig. E	-	46	-	
Turn-on energy	E_{on}	Energy losses include “tail” and diode reverse recovery.	-	0.69	-	mJ
Turn-off energy	E_{off}		-	0.77	-	
Total switching energy	E_{ts}		-	1.46	-	

Anti-Parallel Diode Characteristic

Diode reverse recovery time	t_{rr}	$T_j=25^\circ\text{C}$,	-	143	-	ns
Diode reverse recovery charge	Q_{rr}	$V_R=400\text{V}$, $I_F=30\text{A}$,	-	0.92	-	μC
Diode peak reverse recovery current	I_{rrm}	$di_F/dt=910\text{A}/\mu\text{s}$	-	16.3	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	603	-	$\text{A}/\mu\text{s}$

Switching Characteristic, Inductive Load, at $T_j=175^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=175^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=30\text{A}$, $V_{GE}=0/15\text{V}$,	-	24	-	ns
Rise time	t_r	$r_G=10.6\Omega$,	-	26	-	
Turn-off delay time	$t_{d(off)}$	$L_\sigma=136\text{nH}$, $C_\sigma=39\text{pF}$	-	292	-	
Fall time	t_f	L_σ , C_σ from Fig. E	-	90	-	
Turn-on energy	E_{on}	Energy losses include “tail” and diode reverse recovery.	-	1.0	-	mJ
Turn-off energy	E_{off}		-	1.1	-	
Total switching energy	E_{ts}		-	2.1	-	

Anti-Parallel Diode Characteristic

Diode reverse recovery time	t_{rr}	$T_j=175^\circ\text{C}$	-	225	-	ns
Diode reverse recovery charge	Q_{rr}	$V_R=400\text{V}$, $I_F=30\text{A}$,	-	2.39	-	μC
Diode peak reverse recovery current	I_{rrm}	$di_F/dt=910\text{A}/\mu\text{s}$	-	22.3	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	310	-	$\text{A}/\mu\text{s}$

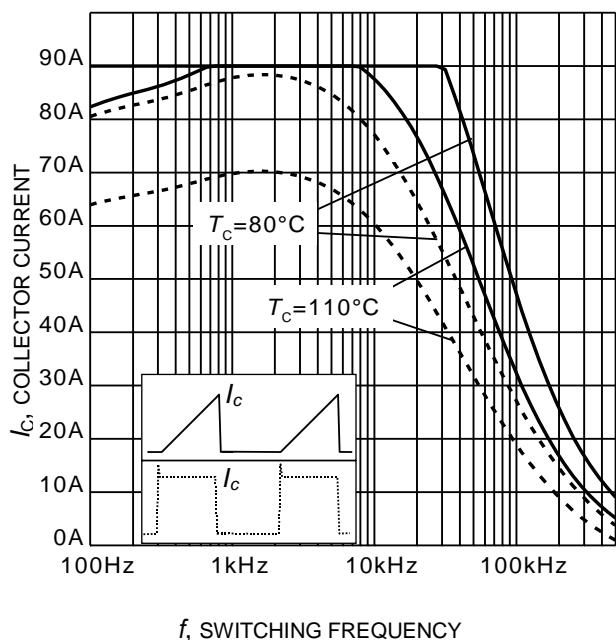


Figure 1. Collector current as a function of switching frequency
 $(T_j \leq 175^\circ\text{C}, D = 0.5, V_{CE} = 400\text{V}, V_{GE} = 0/15\text{V}, r_G = 10\Omega)$

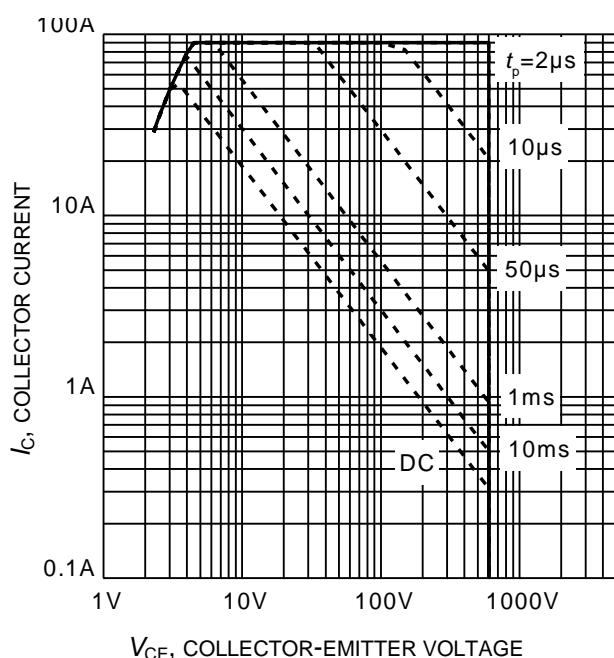


Figure 2. Safe operating area
 $(D = 0, T_C = 25^\circ\text{C}, T_j \leq 175^\circ\text{C}; V_{GE}=0/15\text{V})$

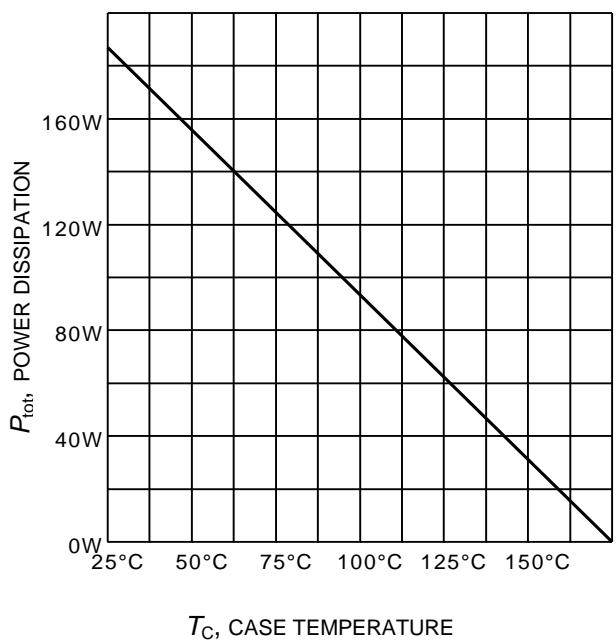


Figure 3. Power dissipation as a function of case temperature
 $(T_j \leq 175^\circ\text{C})$

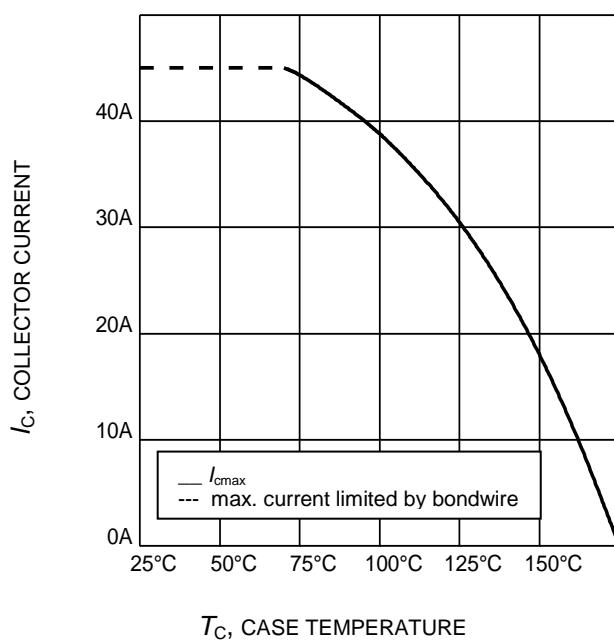


Figure 4. Collector current as a function of case temperature
 $(V_{GE} \geq 15\text{V}, T_j \leq 175^\circ\text{C})$

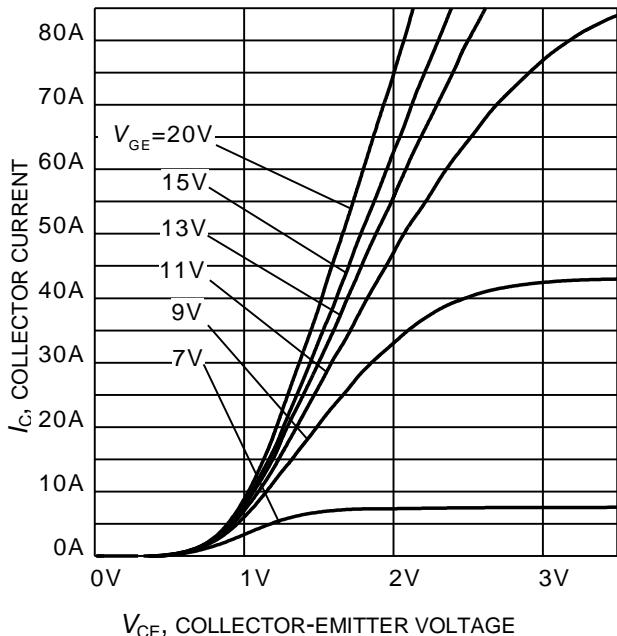


Figure 5. Typical output characteristic
($T_j = 25^\circ\text{C}$)

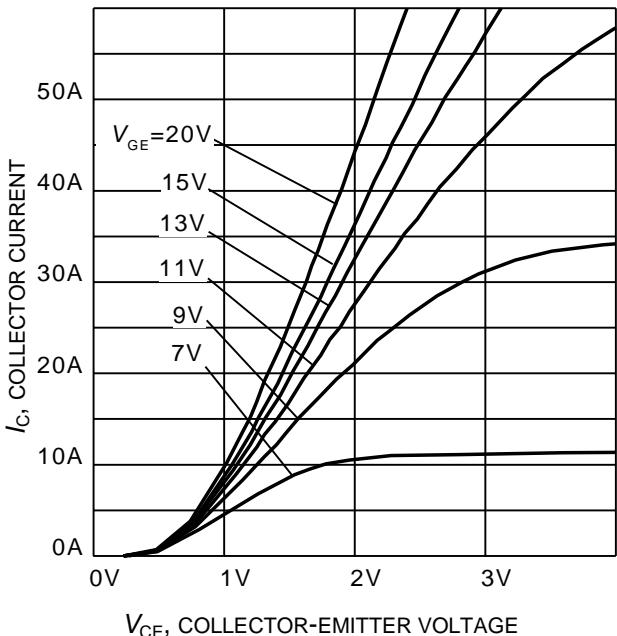


Figure 6. Typical output characteristic
($T_j = 175^\circ\text{C}$)

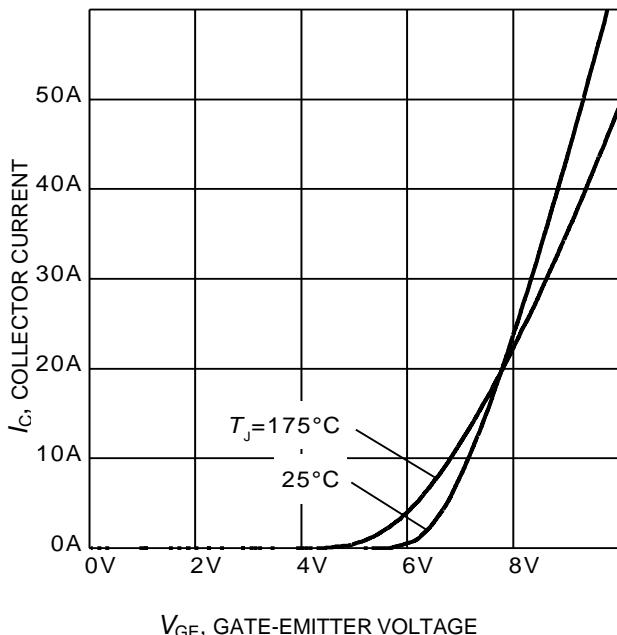


Figure 7. Typical transfer characteristic
($V_{CE} = 10\text{V}$)

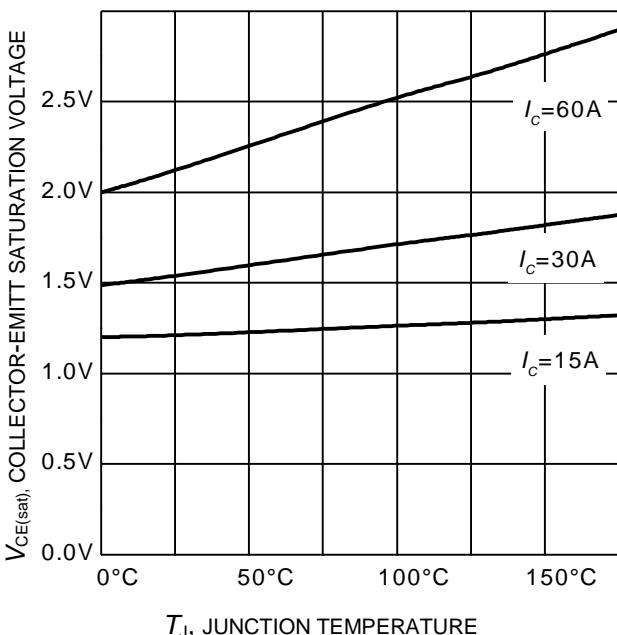


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

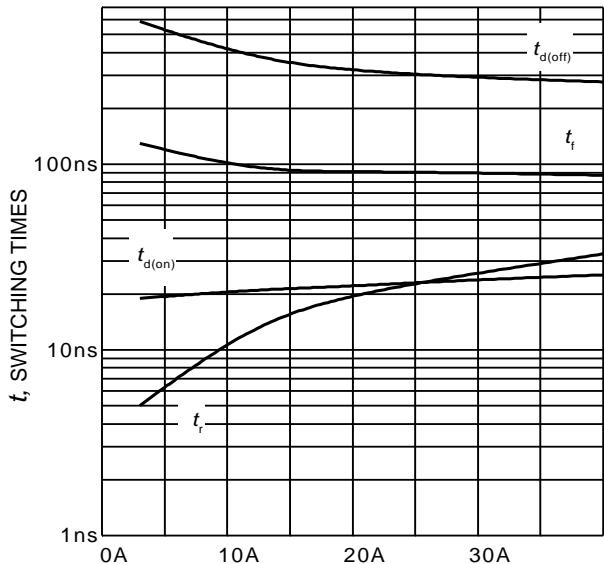

 I_C , COLLECTOR CURRENT

Figure 9. Typical switching times as a function of collector current
 (inductive load, $T_J=175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $r_G = 10\Omega$,
 Dynamic test circuit in Figure E)

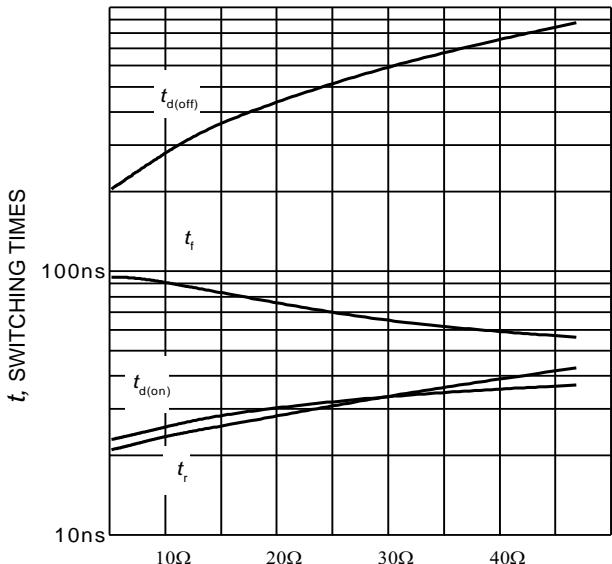

 R_G , GATE RESISTOR

Figure 10. Typical switching times as a function of gate resistor
 (inductive load, $T_J = 175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $I_C = 30\text{A}$,
 Dynamic test circuit in Figure E)

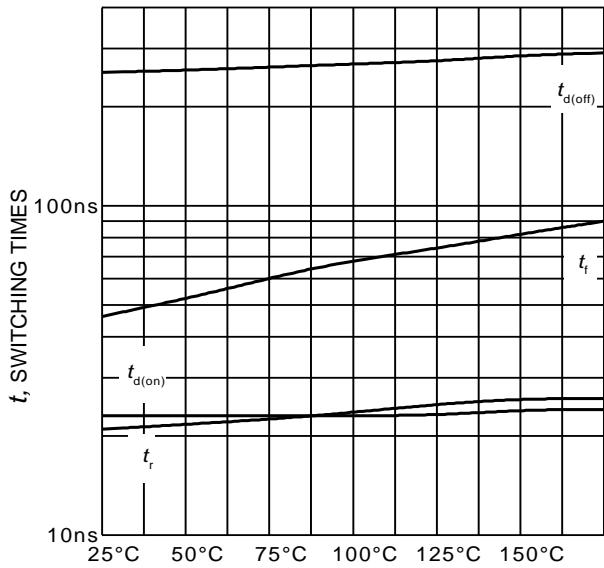

 T_J , JUNCTION TEMPERATURE

Figure 11. Typical switching times as a function of junction temperature
 (inductive load, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/15\text{V}$, $I_C = 30\text{A}$, $r_G = 10\Omega$,
 Dynamic test circuit in Figure E)

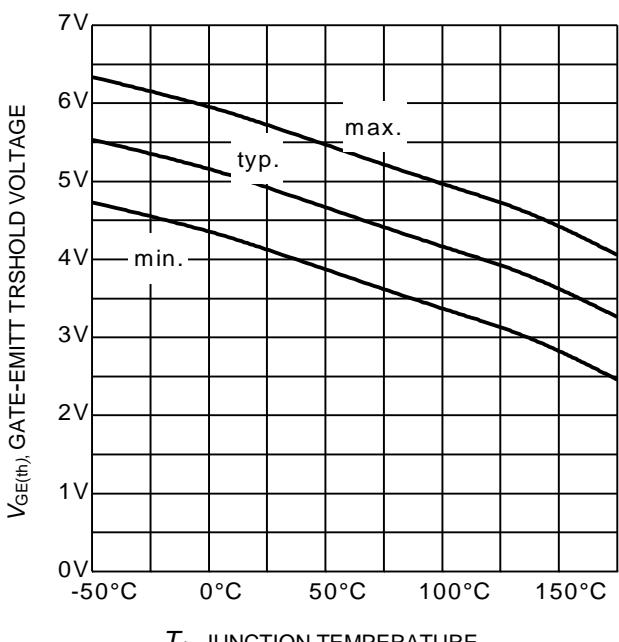

 T_J , JUNCTION TEMPERATURE

Figure 12. Gate-emitter threshold voltage as a function of junction temperature
 $(I_C = 0.43\text{mA})$

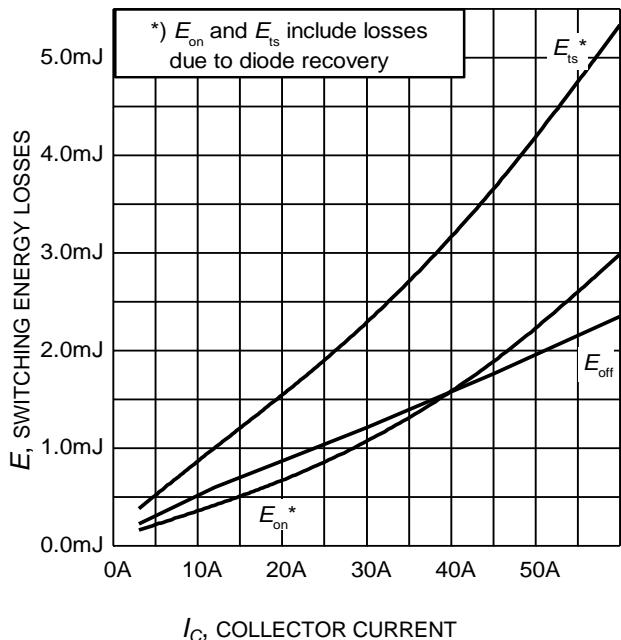


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, $T_J = 175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $r_G = 10\Omega$,
Dynamic test circuit in Figure E)

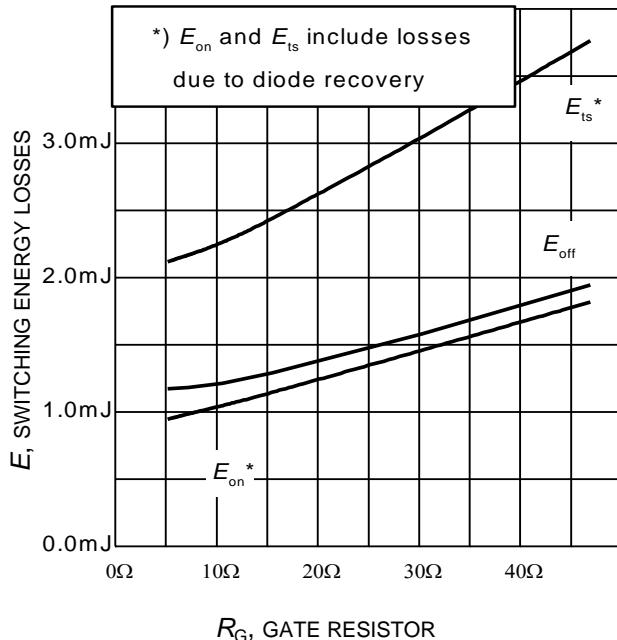


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, $T_J = 175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $I_C = 30\text{A}$,
Dynamic test circuit in Figure E)

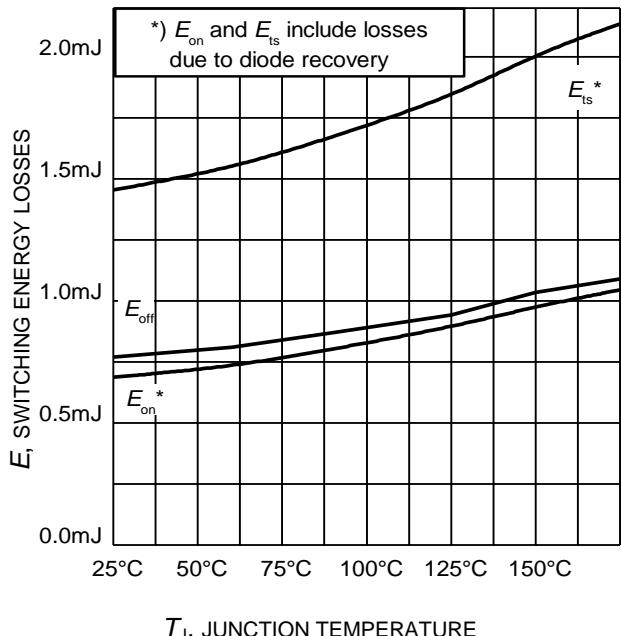


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/15\text{V}$, $I_C = 30\text{A}$, $r_G = 10\Omega$,
Dynamic test circuit in Figure E)

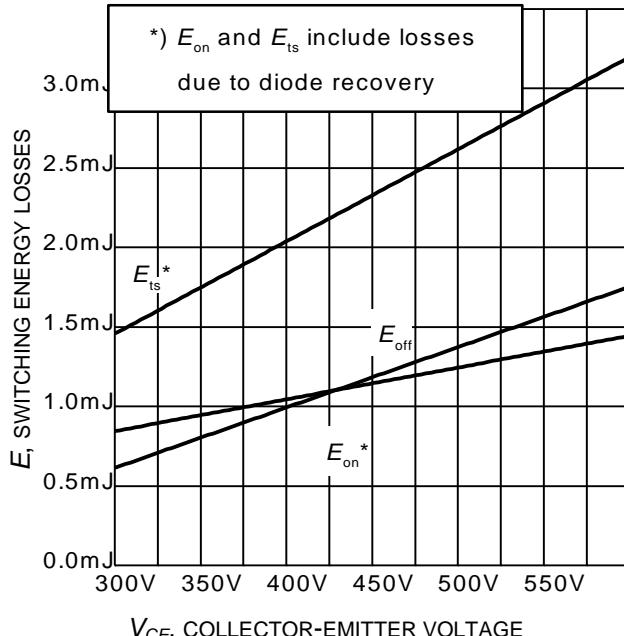


Figure 16. Typical switching energy losses as a function of collector-emitter voltage
(inductive load, $T_J = 175^\circ\text{C}$,
 $V_{GE} = 0/15\text{V}$, $I_C = 30\text{A}$, $r_G = 10\Omega$,
Dynamic test circuit in Figure E)

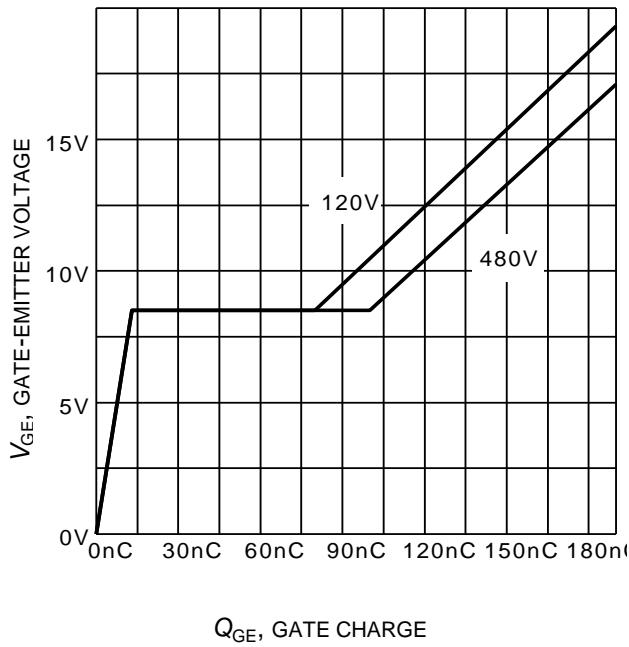


Figure 17. Typical gate charge
($I_C=30$ A)

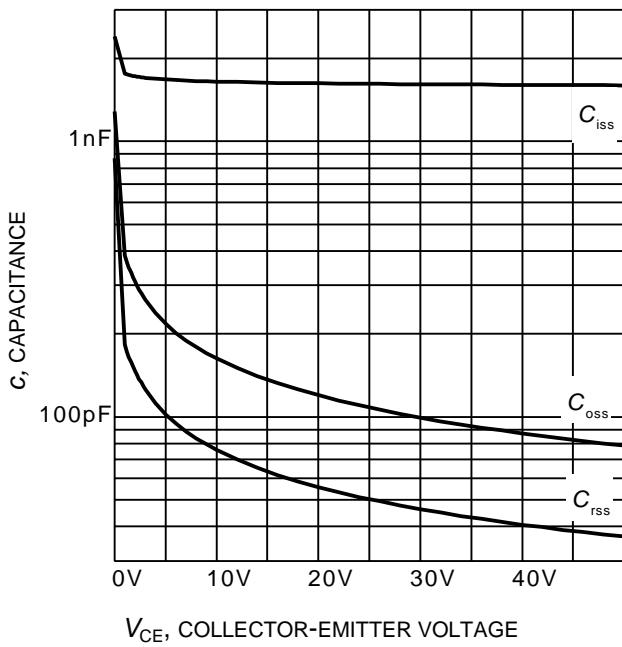


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE}=0$ V, $f = 1$ MHz)

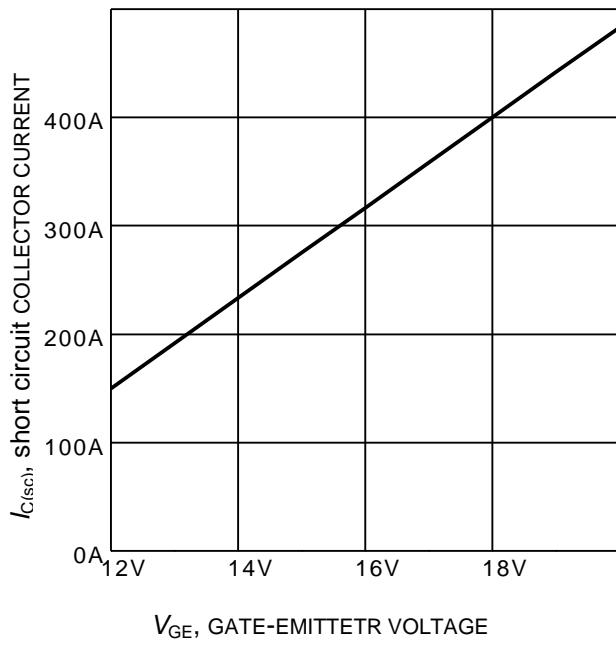


Figure 19. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 400$ V, $T_j \leq 150^\circ\text{C}$)

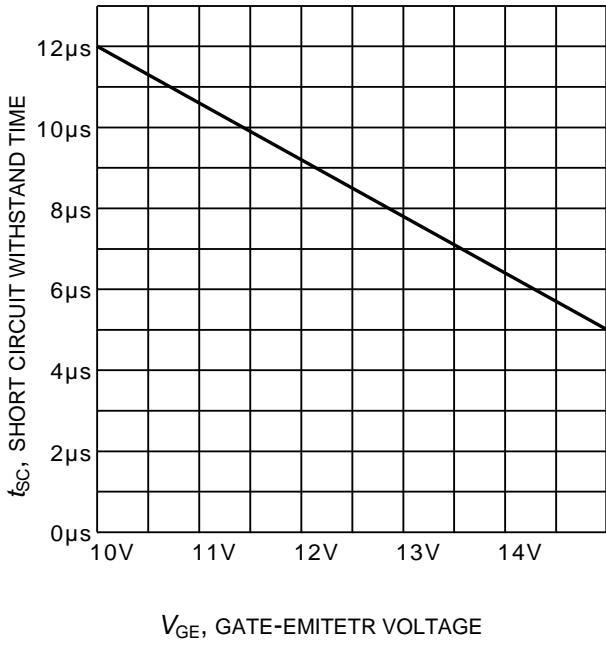
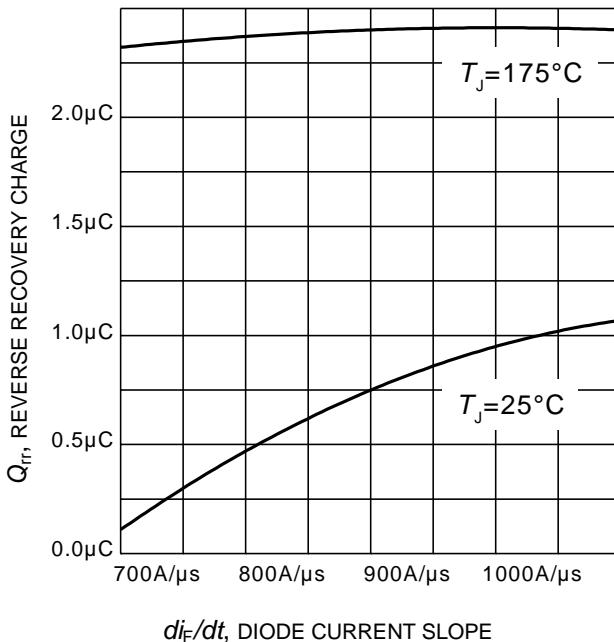
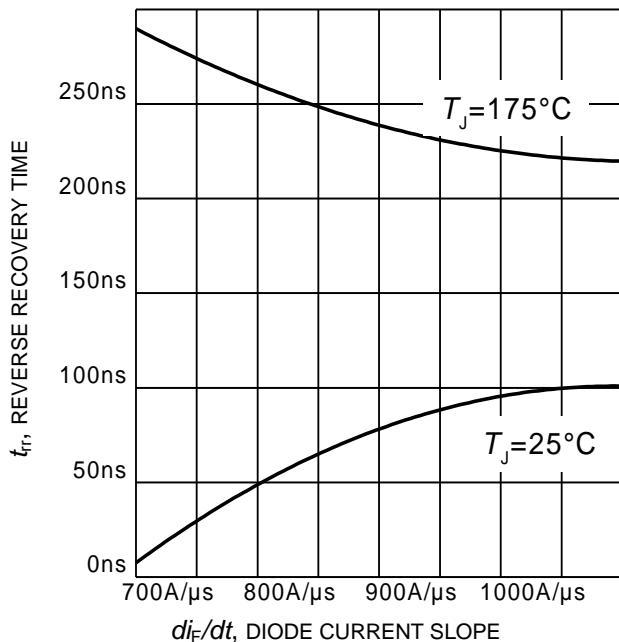
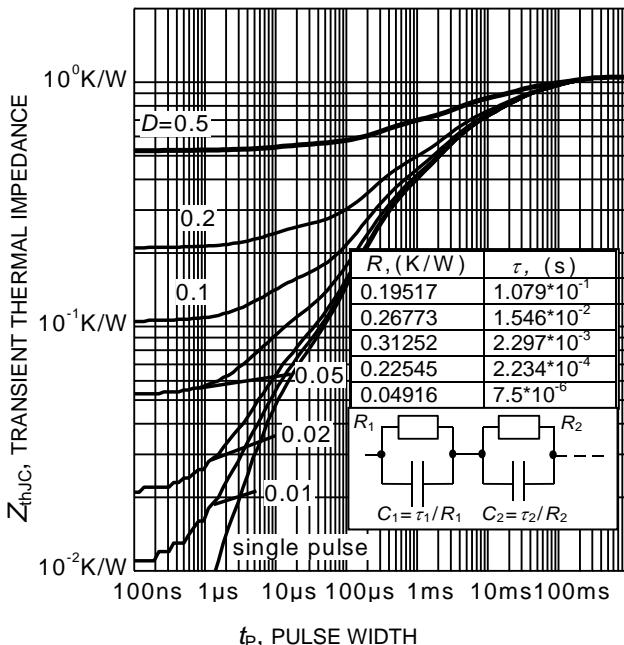
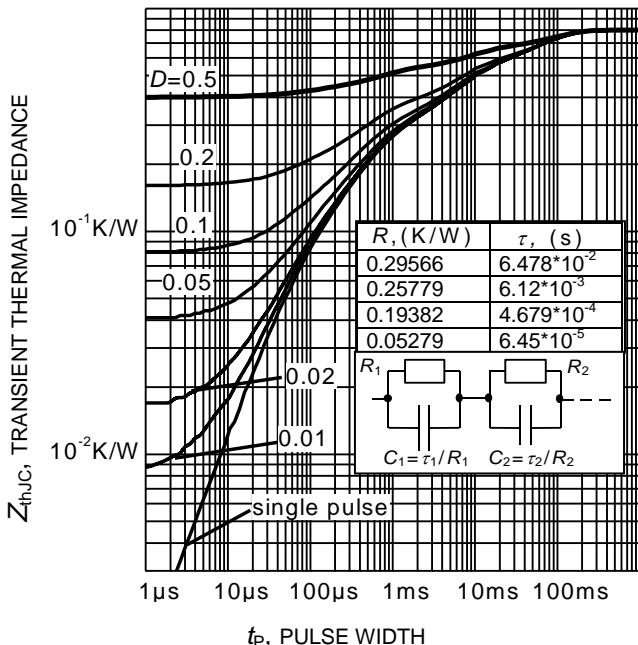
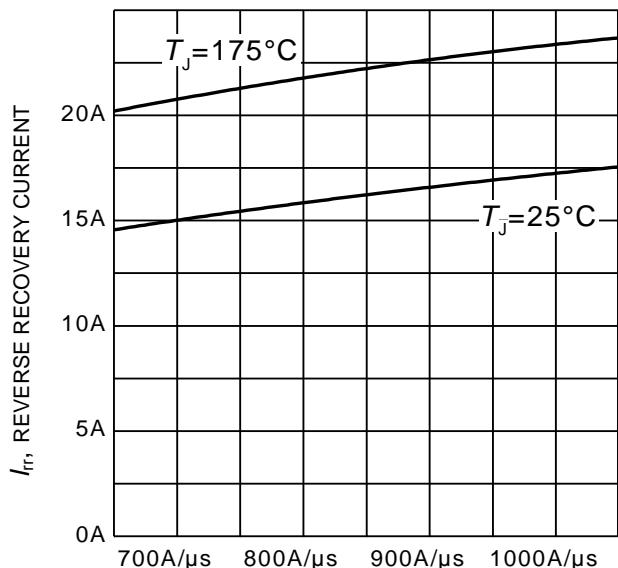


Figure 20. Short circuit withstand time as a function of gate-emitter voltage
($V_{CE}=400$ V, start at $T_j=25^\circ\text{C}$, $T_{jmax}<150^\circ\text{C}$)

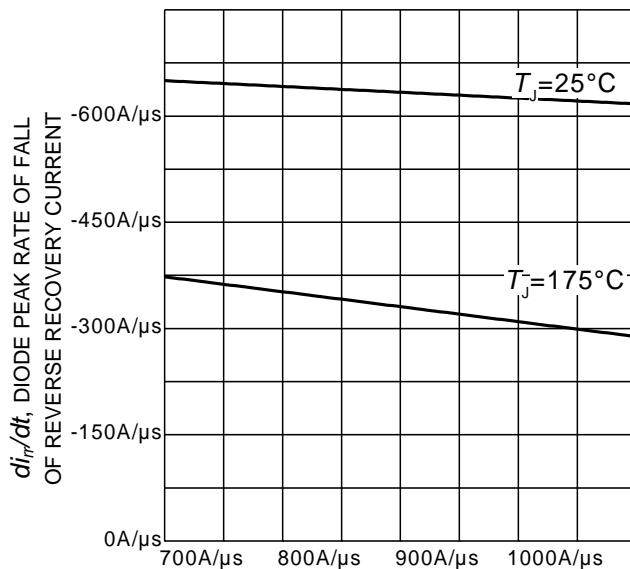




di_F/dt , DIODE CURRENT SLOPE

Figure 25. Typical reverse recovery current as a function of diode current slope

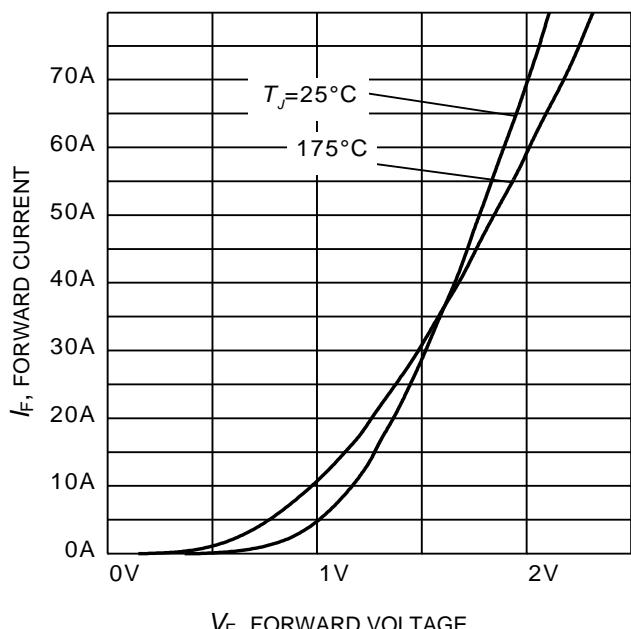
($V_R = 400V$, $I_F = 30A$,
Dynamic test circuit in Figure E)



di_F/dt , DIODE CURRENT SLOPE

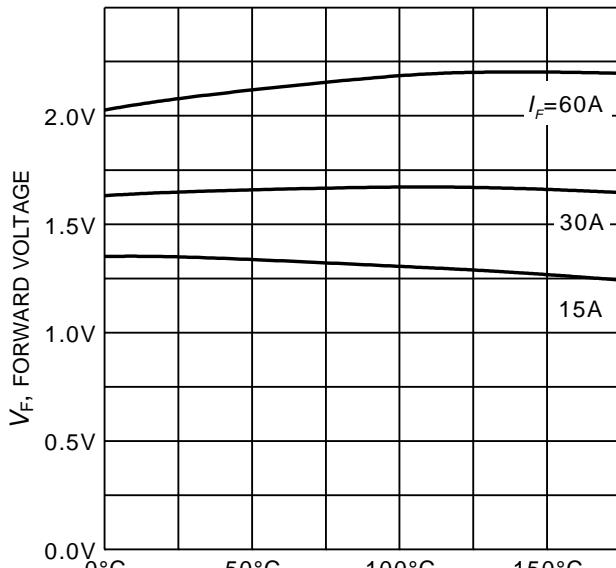
Figure 26. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

($V_R=400V$, $I_F=30A$,
Dynamic test circuit in Figure E)



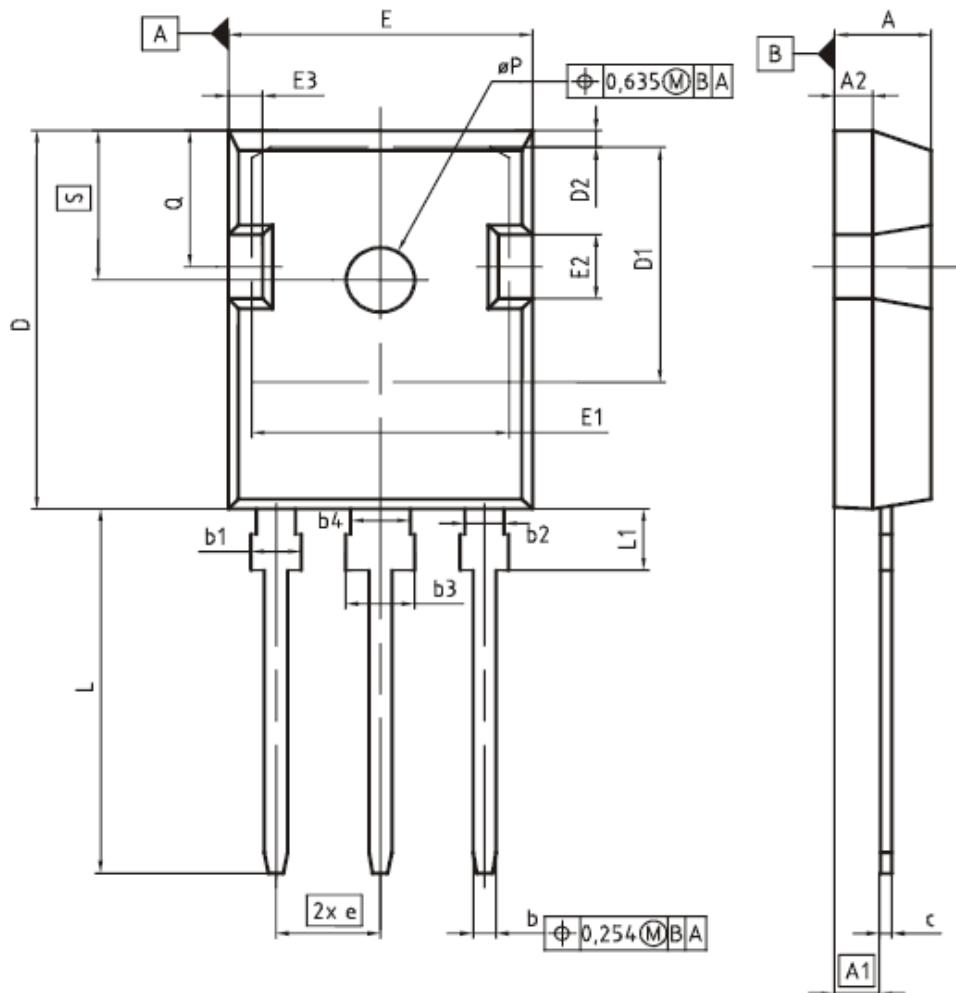
V_F , FORWARD VOLTAGE

Figure 27. Typical diode forward current as a function of forward voltage



T_J , JUNCTION TEMPERATURE

Figure 28. Typical diode forward voltage as a function of junction temperature

PG-T0247-3


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4,83	5,21	0,190	0,205
A1	2,27	2,54	0,089	0,100
A2	1,85	2,16	0,073	0,085
b	1,07	1,33	0,042	0,052
b1	1,90	2,41	0,075	0,095
b2	1,90	2,16	0,075	0,085
b3	2,87	3,38	0,113	0,133
b4	2,87	3,13	0,113	0,123
c	0,55	0,68	0,022	0,027
D	20,80	21,10	0,819	0,831
D1	16,25	17,65	0,640	0,695
D2	0,95	1,35	0,037	0,053
E	15,70	16,13	0,618	0,635
E1	13,10	14,15	0,516	0,557
E2	3,68	5,10	0,145	0,201
E3	1,00	2,60	0,039	0,102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19,80	20,32	0,780	0,800
L1	4,10	4,47	0,161	0,176
øP	3,50	3,70	0,138	0,146
Q	5,49	6,00	0,216	0,236
S	6,04	6,30	0,238	0,248

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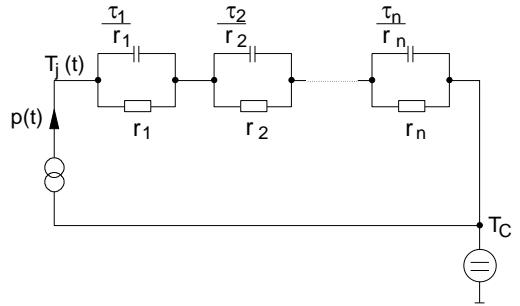
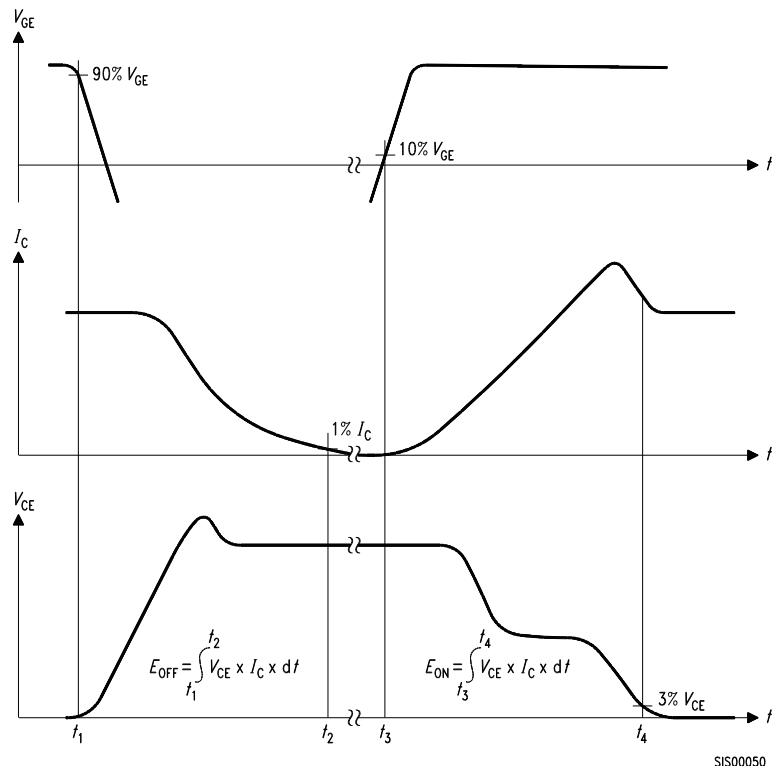
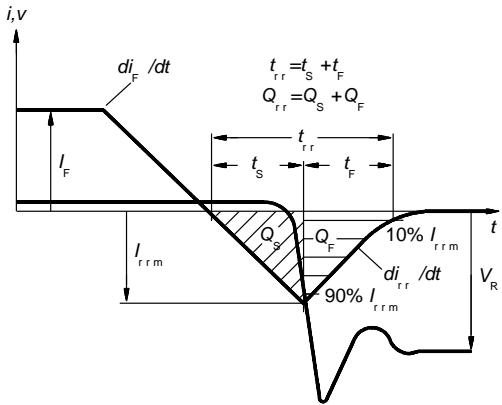
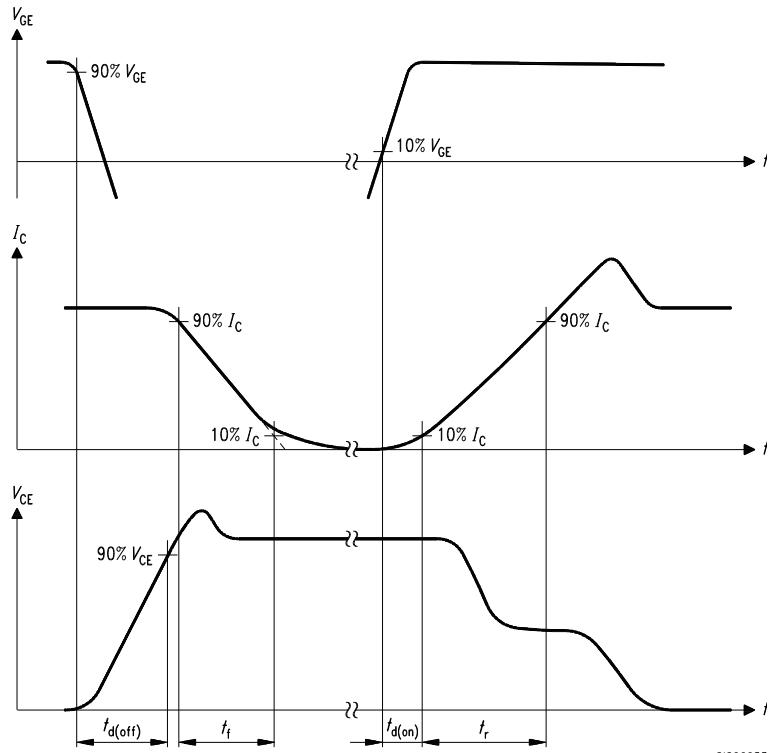


Figure D. Thermal equivalent circuit

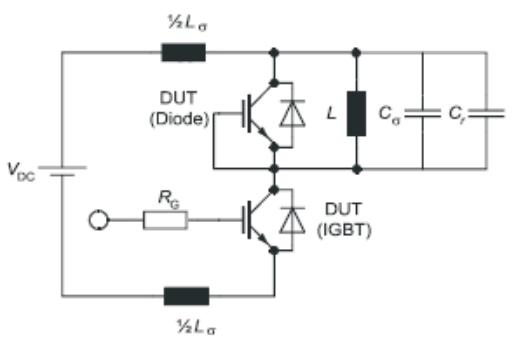


Figure E. Dynamic test circuit
 Parasitic inductance L_α ,
 Parasitic capacitor C_α ,
 Relief capacitor C_r
 (only for ZVT switching)



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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помошь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помошь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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